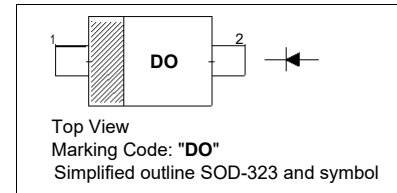


**MA721WS SILICON EPITAXIAL SCHOTTKY BARRIER DIODE****Applications**

- Super-high speed switching circuit
- Small current rectification

**PINNING**

PIN	DESCRIPTION
1	Cathode
2	Anode

**Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )**

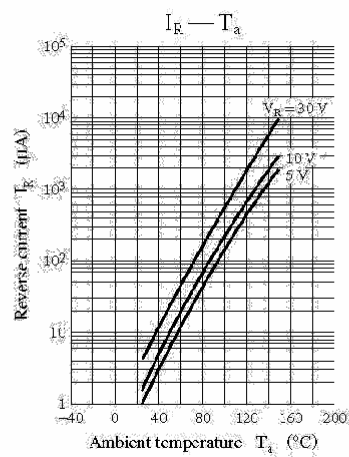
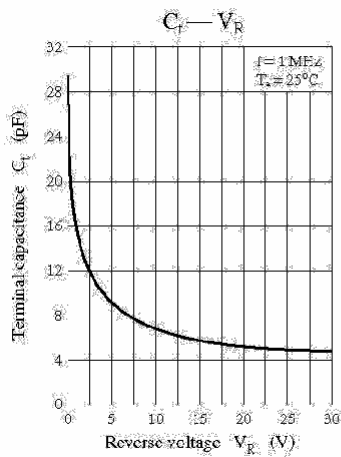
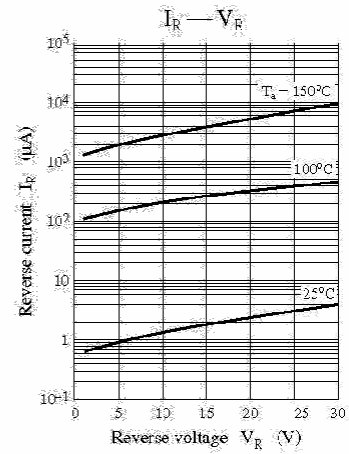
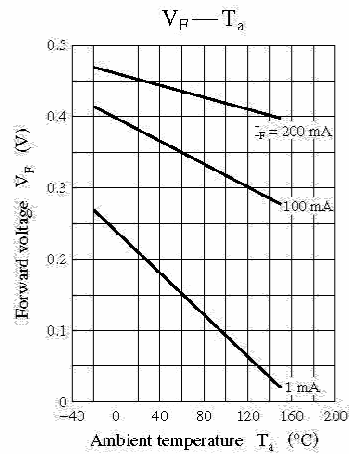
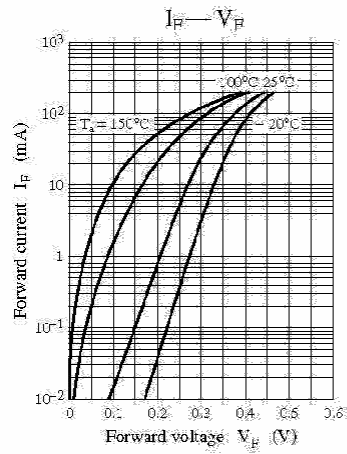
Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	30	V
Peak Forward Current	$I_{FM}$	300	mA
Average Forward Current	$I_{F(AV)}$	200	mA
Non-repetitive Peak Forward Surge Current <sup>1)</sup>	$I_{FSM}$	1	A
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

<sup>1)</sup> The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

**Characteristics at  $T_a = 25^\circ\text{C}$** 

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	$V_F$	-	0.55	V
Reverse Current at $V_R = 30\text{ V}$	$I_R$	-	50	$\mu\text{A}$
Terminal Capacitance at $f = 1\text{ MHz}$	$C_T$	30	-	pF
Reverse Recovery Time at $I_F = I_R = 100\text{ mA}$ , $I_{rr} = 10\text{ mA}$ , $R_L = 100\ \Omega$	$t_{rr}$	3	-	ns

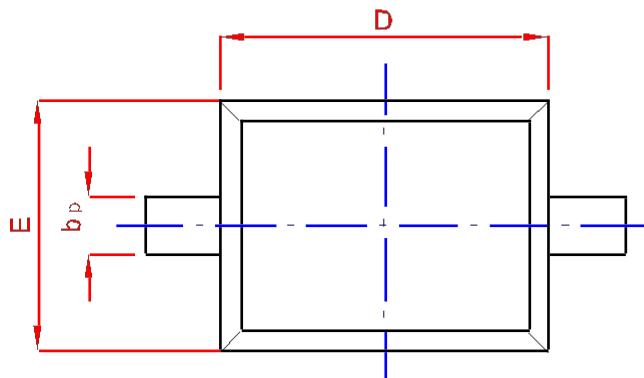
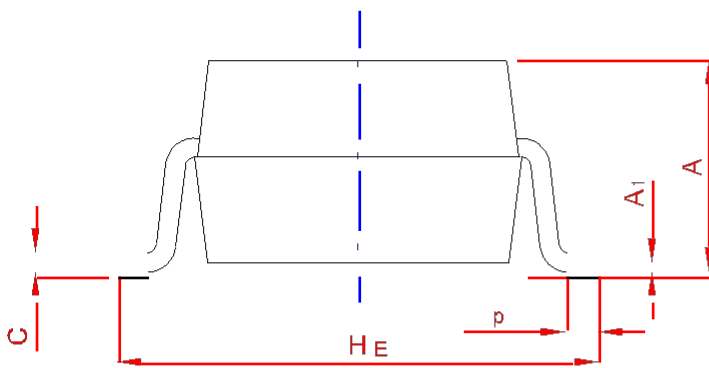
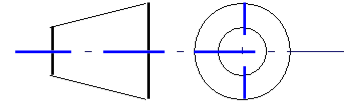
## Typical Characteristics



## PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



UNIT	A	b <sub>p</sub>	C	D	E	H <sub>E</sub>	A <sub>1</sub>	L <sub>p</sub>
mm	1.20 0.90	0.40 0.25	0.15 0.10	1.80 1.60	1.35 1.15	2.80 2.30	0.10 0.01	0.50 0.20